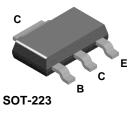
**BCP54** 



# **BCP54**



# NPN General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switching circuits requiring collector currents to 1.2 A. Sourced from Process 38.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	45	V
V <sub>CBO</sub>	Collector-Base Voltage	45	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	1.5	А
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES: 1) These ratings are based on a maximum junction temperature of 150 degrees C. 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# Thermal Characteristics TA = 25°C unless otherwise noted

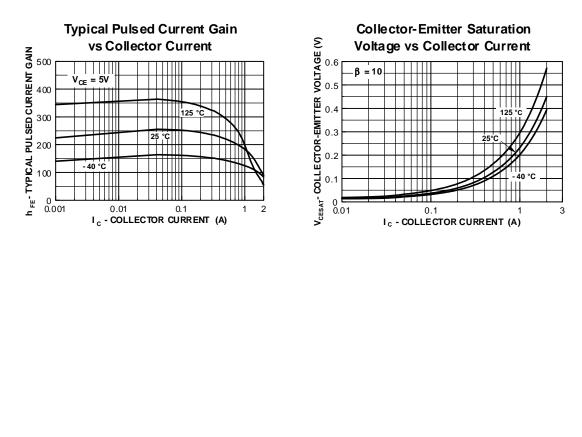
Symbol	Characteristic	Max	Units
		BCP54	
P <sub>D</sub>	Total Device Dissipation	1.5	W
	Derate above 25°C	12	mW/°C
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	83.3	°C/W

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# **NPN General Purpose Amplifier** (continued)

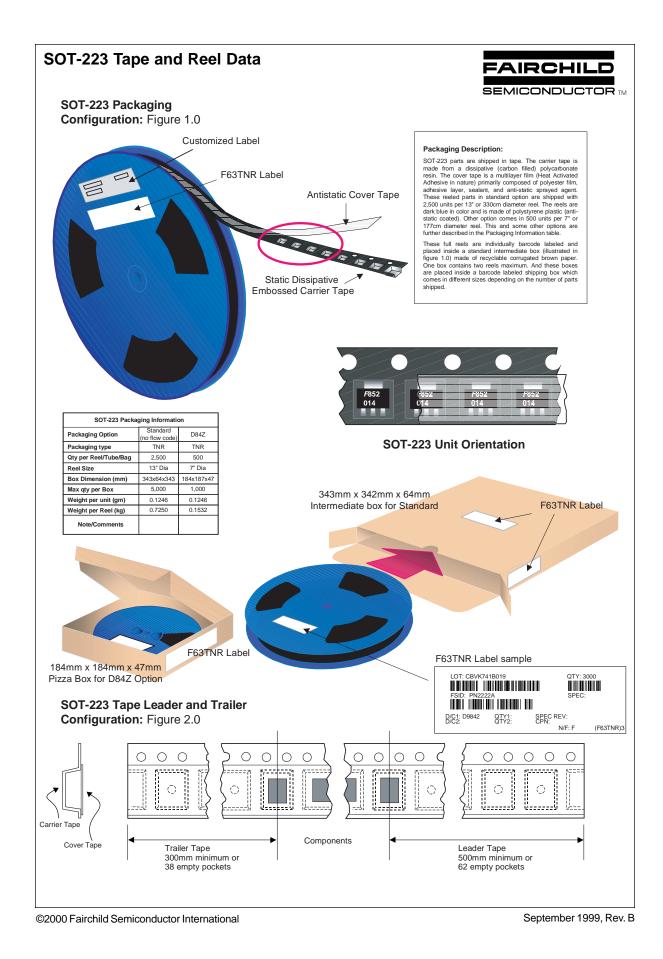
**BCP54** 

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	45		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	45		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \mu {\rm A},  I_{\rm C} = 0$	5.0		V
I <sub>CBO</sub>	Collector-Cutoff Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$		100	nA
·CBU					
СВО		$V_{CB} = 30 \text{ V}, I_E = 0, T_A = 125^{\circ}\text{C}$		10	μΑ
I <sub>EBO</sub>	Emitter-Cutoff Current	$V_{CB} = 30 \text{ V}, I_E = 0, T_A = 125^{\circ}\text{C}$ $V_{EB} = 5.0 \text{ V}, I_C = 0$		10 10	μA μA
I <sub>EBO</sub> ON CHAF	Emitter-Cutoff Current RACTERISTICS DC Current Gain	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$	25	-	· ·
ЕВО	RACTERISTICS	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$ $I_{C} = 5.0 \text{ mA}, V_{CE} = 2.0 \text{ V}$ $I_{C} = 150 \text{ mA}, V_{CE} = 2.0 \text{ V}$	25 40	-	· ·
EBO ON CHAF	RACTERISTICS	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$ $I_{C} = 5.0 \text{ mA}, V_{CE} = 2.0 \text{ V}$	_	10	· ·
DN CHAF	RACTERISTICS	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$ $I_{C} = 5.0 \text{ mA}, V_{CE} = 2.0 \text{ V}$ $I_{C} = 150 \text{ mA}, V_{CE} = 2.0 \text{ V}$	40	10	· ·

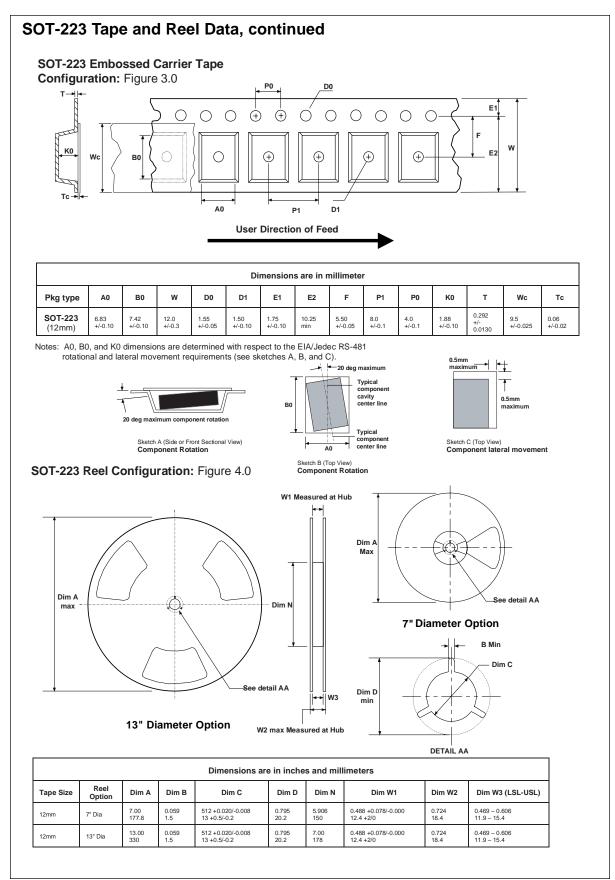


BCP54

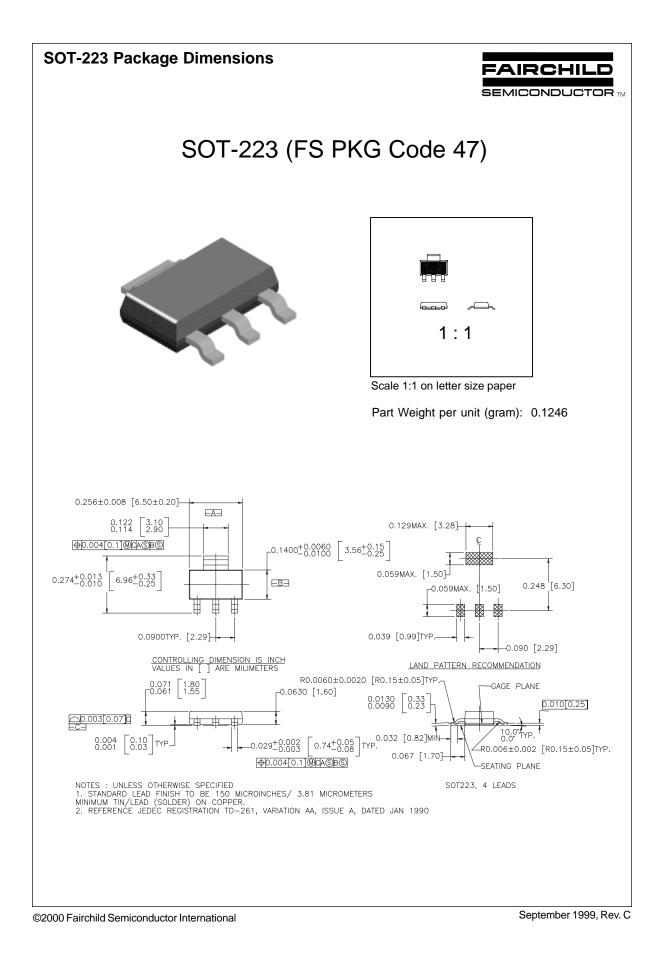
#### **NPN General Purpose Amplifier** (continued) **Typical Characteristics** (continued) **Base-Emitter Saturation Base-Emitter ON Voltage vs** Voltage vs Collector Current **Collector Current** Vector BASE-EMITTER ON VOLTAGE (V) 100000 10000 10000 10000 10000 V 88.5 - EASE-EMITTER VOLTAGE (V) 10 °C . 25°C 40 °C TH 125 °C 125 °C нт 'CE Ш 0.01 0.1 10 100 1000 I<sub>c</sub> - COLLECTOR CURRENT (A) I<sub>c</sub> - COLLECTOR CURRENT (mA) **Collector-Base Capacitance** Collector-Cutoff Current 080 - COLLECTOR-BASE CAPACITANCE (pF) 0 0 0 0 0 0 0 0 0 vs Collector-Base Voltage vs Ambient Temperature Icao-COLLECTOR CURRENT (nA) 40V CB= 25 50 75 100 125 150 12 16 20 0 24 28 VCB - COLLECTOR-BASE VOLTAGE (V) T<sub>A</sub> - AM BIENT TE MPE RATURE (°C) **Power Dissipation vs Gain Bandwidth Product Ambient Temperature** vs Collector Current 1.5 <sub>CE</sub> = 10V **L** 1.2! **L** 1 SOT-223 $\pi$ 0 10 100 Ic - COLLECTOR CURRENT (mA) 1 1000 50 75 100 TEMPERATURE (°C) 0 25 125 150



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## PRODUCT STATUS DEFINITIONS

Definition of Terms

Product Status	Definition	
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	Formative or In Design First Production Full Production	